IN THE SPECIFICATION

Please amend paragraph (0004) beginning at page 2, as follows:

The light extraction efficiency of this organic EL light-emitting device is expected to be low. Specifically, the refractive index of ITO (indium tin oxide) used as the transparent electrode is about 2.0 higher than the refractive index 1.5 of the glass substrate used as the transparent substrate. ~~Therefore,the~~ Therefore, the greater proportion of the light proceeding toward the glass substrate from the transparent electrode becomes a transparent electrode waveguide mode propagates through the neighborhood of the transparent electrode and fails to be radiated to the glass substrate from the transparent electrode. Fig. 1 shows the result of simulation of the electric field distribution in the transparent electrode waveguide mode trapped in the transparent electrode. In Fig. 1, in accordance with the distance from the metal electrode, the refractive index distributions of the ITO and the glass substrate are indicated by dashed lines following Alq3 and PVK making up an organic EL layer, while the field intensity in the transparent electrode waveguide mode of the light having the light emission wavelength of 524 nm is indicated by solid line. As understood from Fig. 1, although the exudation of about the effective wavelength is observed, the transparent electrode waveguide mode is trapped by the ITO high in refractive index and cannot be extracted externally.

Please amend paragraph (0024) beginning at page 10, as follows:

The light-emitting device according to the second aspect of the invention also includes an organic EL light-emitting device characterized in that the second electrode is a transparent electrode, a thin metal electrode or an electrode constituting of the transparent electrode and a thin film which arranged on the transparent electrode at the side of the [[the]] organic EL layer.

Please amend paragraph (0106) beginning at page 44, as follows:

The mode conversion means 41 shown in Fig. 19 can be fabricated by two separate growth sessions while forming the organic EL layer 32 by the spin coat method, vacuum vapor deposition, coating or the ink jet method. The mode conversion means 41 shown in Figs. 20 to 22, on the other hand, can be formed by etching the surface of the transparent electrode 33, then the organic EL layer 32 and the metal electrode 31 are formed on the upper surface of the transparent electrode thereby to ~~fablicate~~ fabricate the organic EL light-emitting device. The organic EL light-emitting device according to the invention is not limited to the fabrication method described herein.

Please amend paragraph (0115) beginning at page 48, as follows:

In order to mechanically protect or prevent the oxidization or humidification of the metal electrode layer and the organic EL layer of the organic EL light-emitting device, a transparent insulating film is formed effectively as a protective film on the outside of the metal electrode layer. An example of the organic EL light-emitting device having the transparent insulating film is shown in Figs. 30 to 36. In Figs. 30 to 36, numeral 31 denotes a metal electrode, 32 an organic EL layer, 33 a transparent electrode, 34 a transparent substrate, 35 a transparent insulating film as a protective film and 41 mode conversion means. The organic EL light-emitting devices shown in Figs. 30, 31, 32 correspond to the organic EL light-emitting device shown in Figs. 27, 28, 29, respectively, on which the transparent insulating film 35 is formed. These transparent insulating films 35 protect the metal electrode 31 or the organic EL layer 32. The transparent insulating film is formed not only in this case, but by forming the transparent insulating film on the outside of the metal electrode of the organic EL light-emitting device described above, the metal electrode is protected. These transparent insulating films can be formed by sputtering, vapor ~~deposition,vapor~~

~~depostion polymerization,electron~~ deposition, vapor deposition polymerization, electron beam evaporation, plasma deposition, ion plating, CVD, plasma CVD, thermal CVD, etc. using such a material as SiO_x, SiN_x, SiON, SiC, Al_2O_3, AlN, ZnO, MgO_x, TiO_x, ZrO_x, AlO_x, Ta_2O_5, TaO_x, YO_x or WO_x. The transparent insulating film can also be formed by coating or spin coating epoxy resin, acryl resin, polyparaxylene, fluorine-group polymer or polyimide antecedent, followed by setting under ultraviolet curing procedure.

Please amend paragraph (0157) beginning at page 68, as follows:

Examples of the material of the hole injection layer and the hole transport layer include pentacene, tetracene, anthracene, phthalocyanine, ~~α-sexithionphene~~ α-sexithiophene, α, ω-dihexyl-sexithiophene, oligophenylene, ~~oligopheylenevinilene~~ oligophenylenevinylene, dihexyl-anthradithiophene, bis (dithienothiophene), poly(3-hexylthiophene), poly(3-butylthiophene), ~~poly(phenylenevinilene)~~ poly(phenylenevinylene), ~~poly(thienylenevinilene)~~ poly(thienylenevinylene), polyacetylene, α, ω-dihexyl-quinquethiophene, TPD, α-NPD, m-MTDATA, TPAC, TCTA, ~~polyvinylcarbozole~~ polyvinylcarbazole, PDA, CuPc, STB, MTDATA, PEDOT-PSS or TPDPES-TBPAH.

Please amend paragraph (0162) beginning at page 69, as follows:

In the case where the optical film is formed as an optical function element on the surface of the organic EL light-emitting device, [[PMA]] PMMA (polymethylmethacrylate), TAC ~~(tricetate)~~ (triacetate), PVA (polyvinyl alcohol), PC (polycarbonate), acryl, polyethylene terephthalate, polyvinylene, ~~triacethyl ceollulose~~ triacetyl cellulose, cyclo olefin, UV cured resin or liquid crystal polymer is coated or spin coated into a sheet or formed into a sheet by biaxial orientation, casting or extrusion, followed by attaching with heat or adhesive, thereby forming an organic EL light-emitting device. The mode conversion

means in the interior or the boundary of the optical film can be formed by photolithography, soft lithography or transfer.